TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

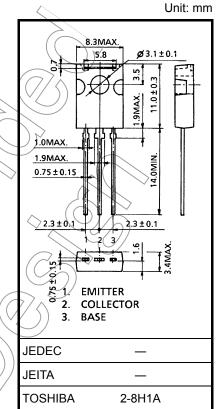
# 2SA1358

Audio Frequency Power Amplifier Applications

- Complementary to 2SC3421
- Suitable for driver of 60 to 80 watts
- High breakdown voltage

#### Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	-120	$(\mathcal{N})$	$\sim$
Collector-emitter voltage		V <sub>CEO</sub>	-120	$\langle \psi \rangle$	
Emitter-base voltage		V <sub>EBO</sub>	-5	V	
Collector current		Ι <sub>C</sub>	-1	Â	
Base current		Ι <sub>Β</sub>	-100	∽ mA	
Collector power dissipation	Ta = 25°C	De	1.5	W	
	Tc = 25°C	PC		VV	/
Junction temperature		Tj	150	< <sup></sup> ℃	
Storage temperature range		T <sub>stg</sub>	-55 to 150	ઝ	$\sim$



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

Weight: 0.82 g (typ.)

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

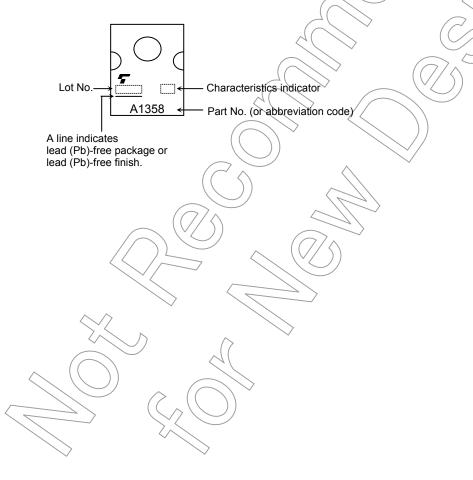
2006-11-09

#### **Electrical Characteristics (Tc = 25°C)**

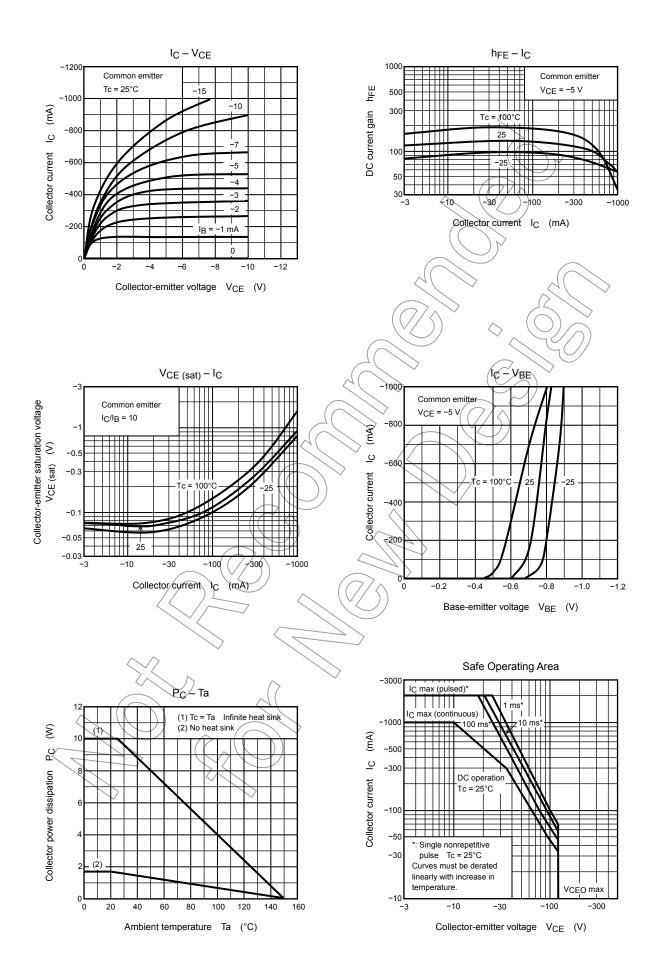
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -120 \text{ V}, I_E = 0$	_	_	-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5 V, I <sub>C</sub> = 0	_	_	-100	nA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{\rm C}$ = -10 mA, $I_{\rm B}$ = 0	-120	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_{\rm E} = -1  {\rm mA},  I_{\rm C} = 0$	-5		_	V
DC current gain	h <sub>FE</sub> (Note)	$V_{CE} = -5 V, I_C = -100 mA$	80	)^_	240	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = −500 mA, I <sub>B</sub> = −50 mA	$\bigcirc$	-0.40	-1.0	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -500 mA		-0.77	-1.0	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -100 mA	_	120	_	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	30	-	pF

Note: hFE classification O: 80 to 160, Y: 120 to 240

#### Marking



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